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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yongxun LIU, et al.
SERIAL NO.: NEW U.S. PCT APPLICATION
FILED: HEREWITH
INTERNATIONAL APPLICATION NO.: PCT/JP04/18525
INTERNATIONAL FILING DATE: December 6, 2004
FOR: DUAL-GATE FIELD EFFECT TRANSISTOR

**REQUEST FOR PRIORITY UNDER 35 U.S.C. 119
AND THE INTERNATIONAL CONVENTION**

Commissioner for Patents
Alexandria, Virginia 22313


Sir:

In the matter of the above-identified application for patent, notice is hereby given that the applicant claims as priority:

<u>COUNTRY</u>	<u>APPLICATION NO</u>	<u>DAY/MONTH/YEAR</u>
Japan	2003-407935	05 December 2003
Japan	2003-408254	05 December 2003
Japan	2003-408112	05 December 2003

Certified copies of the corresponding Convention application(s) were submitted to the International Bureau in PCT Application No. PCT/JP04/18525. Receipt of the certified copy(s) by the International Bureau in a timely manner under PCT Rule 17.1(a) has been acknowledged as evidenced by the attached PCT/IB/304.

Respectfully submitted,
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